

AMENDMENTS TO THE CLAIMS

1. (CURRENTLY AMENDED) A liquid crystal display device, comprising:

first and second substrates facing and spaced apart from each other;

a first inorganic insulating layer ~~over~~on an inner surface of the first substrate;

a second inorganic insulating layer ~~on~~over the inner surface of the first substrate;

an organic insulating layer between the first and second inorganic insulating layers, the organic insulating layer being disposed below the ~~first~~ second inorganic insulating layer; and

a seal pattern between the ~~first~~second inorganic insulating layer and an inner surface of the second substrate, the seal pattern contacting at least a part of the ~~first~~second inorganic insulating layer.

2. (CANCELED)

3. (PREVIOUSLY PRESENTED) The device of claim 1, wherein the first and second inorganic insulating layers comprise at least one inorganic material selected from the group consisting of silicon nitride (SiN_x), silicon oxide (SiO_2) and silicon oxynitride (SiO_xN_y).

4. (PREVIOUSLY PRESENTED) The device of claim 1, wherein the organic insulating layer comprises at least one organic material selected from the group consisting of benzocyclobutene (BCB), acrylic resin and methacrylic resin.

5. (CURRENTLY AMENDED) A liquid crystal display device, comprising:

first and second substrates facing and spaced apart from each other;

a first inorganic insulating layer ~~over~~on an inner surface of the first substrate;

a second inorganic insulating layer ~~on~~over the inner surface of the first substrate;

an organic insulating layer between the first and second inorganic insulating layers; and

a seal pattern between the ~~first~~second inorganic insulating layer and an inner surface of the second substrate, the seal pattern contacting the ~~first~~second inorganic insulating layer,

wherein the ~~second~~first inorganic insulating layer has at least one groove through the ~~first~~second inorganic insulating layer and the organic insulating layer.

6. (CURRENTLY AMENDED) The device of claim 5, wherein the seal pattern contacts the ~~second~~first inorganic insulating layer through the at least one groove.

7. (ORIGINAL) The device of claim 6, wherein a bottom surface of the at least one groove has an unevenness.

8. (CURRENTLY AMENDED) The device of claim 5, further comprising:

a metal layer between the first substrate and the ~~second~~first inorganic insulating layer.

9. (ORIGINAL) The device of claim 8, wherein the seal pattern contacts the metal layer through the at least one groove.

10. (ORIGINAL) The device of claim 9, further comprising:

a thin film transistor including a gate electrode, an active layer, a source electrode and a drain electrode on the first substrate, wherein the metal layer is the same layer as the gate electrode.

11. (CURRENTLY AMENDED) The device of claim 1, wherein the ~~second~~first inorganic insulating layer has at least one groove through the organic insulating layer.

12. (CURRENTLY AMENDED) The device of claim 11, wherein the ~~first~~second inorganic insulating layer contacts the ~~second~~first inorganic insulating layer through the at least one groove.

13. (WITHDRAWN, CURRENTLY AMENDED) The device of claim 1, further comprising:

a metal layer between the organic insulating layer and the ~~second~~first inorganic insulating layer.

14. (WITHDRAWN, CURRENTLY AMENDED) The device of claim 13, wherein the organic insulating layer has at least one hole through the ~~first~~second inorganic insulating layer and the seal pattern contacts the metal layer through the at least one hole.

15. (WITHDRAWN) The device of claim 14, further comprising:

a thin film transistor including a gate electrode, an active layer, a source electrode and a drain electrode on the first substrate, wherein the metal layer is the same layer as the source and drain electrodes.

16. (WITHDRAWN) A liquid crystal display device, comprising:

first and second substrates facing and spaced apart from each other;

a pixel layer over an inner surface of the first substrate; and

a seal pattern between the pixel layer and an inner surface of the second substrate, the seal pattern contacting the pixel layer.

17. (WITHDRAWN) The device of claim 16, further comprising:

an inorganic insulating layer on the inner surface of the first substrate;

and

an organic insulating layer between the inorganic insulating layer and the pixel layer.

18. (WITHDRAWN) The device of claim 17, further comprising:

a thin film transistor on the first substrate and a pixel electrode connected to the thin film transistor, wherein the pixel layer is the same layer as the pixel electrode.

19. (ORIGINAL) A fabricating method of a liquid crystal display device, comprising:

- forming a thin film transistor on a first substrate;
- forming a passivation layer covering the thin film transistor, and the passivation layer includes an organic material;
- forming an inorganic insulating layer on the passivation layer;
- forming a seal pattern surrounding the thin film transistor; and
- attaching a second substrate to the first substrate such that the seal pattern contacts the inorganic insulating layer and the second substrate.

20. (ORIGINAL) The method of claim 19, wherein a step of forming the thin film transistor comprises:

- forming a gate electrode on the first substrate;
- forming a gate insulating layer on the gate electrode, and the gate insulating layer includes an inorganic material;
- forming an active layer on the gate insulating layer; and
- forming source and drain electrodes on the active layer.

21. (PREVIOUSLY PRESENTED) A fabricating method of a liquid crystal display device, comprising:

forming a thin film transistor on a first substrate, wherein the step of forming the thin film transistor includes forming a gate electrode on the first substrate, forming a gate insulating layer on the gate electrode, and the gate insulating layer includes an inorganic material, forming an active layer on the gate insulating layer, and forming source and drain electrodes on the active layer;

forming a passivation layer covering the thin film transistor, and the passivation layer includes an organic material;

forming an inorganic insulating layer on the passivation layer;

forming a seal pattern surrounding the thin film transistor; and

attaching a second substrate to the first substrate such that the seal pattern contacts the inorganic insulating layer and the second substrate,

wherein the method further comprises forming at least one groove through at least part of the gate insulating layer, the passivation layer and at least part of the inorganic insulating layer.

22. (ORIGINAL) The method of claim 21, wherein the seal pattern contacts the gate insulating layer.

23. (ORIGINAL) The method of claim 21, further comprising:

forming a metal layer between the first substrate and the gate insulating layer.

24. (ORIGINAL) The method of claim 23, wherein the metal layer is simultaneously formed with the gate electrode, and the seal pattern contacts the metal layer.

25. (PREVIOUSLY PRESENTED) The method of claim 20, further comprising:

forming at least one groove through the passivation layer and at least part of the gate insulating layer.

26. (WITHDRAWN) The method of claim 25, wherein the inorganic insulating layer contacts the gate insulating layer.

27. (WITHDRAWN) The method of claim 20, further comprising:

forming a metal layer between the gate insulating layer and the passivation layer; and

forming at least one hole through the inorganic insulating layer and the passivation layer.

28. (WITHDRAWN) The method of claim 27, wherein the metal layer is simultaneously formed with the source and drain electrodes and the seal pattern contacts the metal layer through the at least one hole.

29. (WITHDRAWN) A fabricating method of a liquid crystal display device, comprising:

forming a thin film transistor on a first substrate;

forming a passivation layer covering the thin film transistor, the passivation layer including an organic material;

forming a pixel electrode and a pixel layer on the passivation layer, the pixel electrode being connected to the thin film transistor;

forming a seal pattern surrounding the thin film transistor; and

attaching a second substrate to the first substrate such that the seal pattern contacts the pixel layer and the second substrate.

30. (PREVIOUSLY PRESENTED) The method of claim 19, wherein the inorganic insulating layer comprises at least one inorganic material selected from the group consisting of silicon nitride (SiN_x), silicon oxide (SiO_2) and silicon oxynitride (SiO_xN_y).